

FEATURES

- Low and wide electro-optical bandwidth
- C & L bands
- Low insertion loss
- Low $V\pi$

APPLICATIONS

- Side bands generation
- Interferometric sensing
- Frequency shifting / broadening
- Quantum key distribution
- High data rate telecommunications
- Laser combining
- Pound-Drever-Hall locking (PDH)

OPTIONS

- Low residual intensity modulation
- Low insertion loss
- High electrical input power capability

RELATED EQUIPMENTS

- Matched RF amplifiers
- MX, MXAN, MXER Amplitude modulators
- Short optical pulse ModBox

The MPX-LN and MPZ-LN series make up the most comprehensive range of electro-optic phase modulators available on the market for the 1550 nm wavelength band.

- The MPZ-LN series are ideally suited for high bandwidth operation at 1 GHz, 10 GHz, 20 GHz and up to 40 GHz.
- The MPX-LN-0.1 has a high impedance input optimized for modulation frequencies below 150 MHz.

Designed using state-of-the-art and proven lithium niobate technology, MPX-LN and MPZ-LN phase modulators are easy to operate and to integrate. They offer the highest performance for a wide range of applications from laboratory experiments to demanding industrial systems.

Low and Medium Bandwidth Phase Modulators - Highlights

| Parameter | MPX-LN-0.1 | MPZ-LN-01 |
|---------------------------|-------------------|-----------|
| Operating wavelength | 1530 nm - 1625 nm | |
| Electro-optical bandwidth | 150 MHz | 1.5 GHz |
| $V\pi$ RF @50 kHz | 3.5 V | 3 V |
| Insertion loss | 2.7 dB | 2.5 dB |

Specifications given at 25 °C, 1550 nm.

Wide Bandwidth Phase Modulators - Highlights

| Parameter | MPZ-LN-10 | MPZ-LN-20 | MPZ-LN-40 |
|---------------------------|-------------------|-----------|-----------|
| Operating wavelength | 1530 nm - 1625 nm | | |
| Electro-optical bandwidth | 12 GHz | 25 GHz | 33 GHz |
| $V\pi$ RF @50 kHz | 4 V | 4.5 V | 6 V |
| Insertion loss | 2.5 dB | 2.5 dB | 2.5 dB |

Specifications given at 25 °C, 1550 nm.

MPX-LN-0.1

150 MHz Phase Modulator

Electrical Characteristics

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|-------------------------|---------------------------|-----------|-----|--------|-----|------|
| Electro-optic bandwidth | S_{21} | - | - | 150 | - | MHz |
| Vπ RF @50 kHz | $V\pi RF_{50\text{ kHz}}$ | - | - | 3.5 | 4 | V |
| RF input impedance | Z_{in-RF} | - | - | 10 000 | - | Ω |

Optical Characteristics

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|-----------------------------|-----------|----------------------------|------|------------------------------|------|------|
| Crystal | - | - | | Lithium Niobate X-Cut Y-Prop | | |
| Waveguide process | - | - | | Ti diffusion | | |
| Operating wavelength | λ | - | 1530 | 1550 | 1625 | nm |
| Insertion loss | IL | Without optical connectors | - | 2.7 | 3.5 | dB |
| Polarization dependent loss | PDL | - | - | 5 | 8 | dB |
| Optical return loss | ORL | - | -40 | -45 | - | dB |

All specifications given at 25 °C, 1550 nm, unless differently specified.

Absolute Maximum Ratings

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. These are absolute stress ratings only. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of the data sheet. Exposure to absolute maximum ratings for extended periods can adversely affect device reliability.

| Parameter | Symbol | Min | Max | Unit |
|--------------------------|-----------|-----|-----|------|
| Modulation voltage range | EV_{in} | -20 | 20 | V |
| Optical input power | OP_{in} | - | 20 | dBm |
| Operating temperature | OT | 0 | +70 | °C |
| Storage temperature | ST | -40 | +85 | °C |

MPZ-LN-01 1 GHz Phase Modulator

Electrical Characteristics

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|-------------------------|---------------------------|-----------|-----|-----|-----|------|
| Electro-optic bandwidth | S_{21} | - | 1 | 1.5 | - | GHz |
| Ripple S_{21} | ΔS_{21} | - | - | 0.5 | - | dB |
| Electrical return loss | S_{11} | - | - | -15 | -12 | dB |
| Vπ RF @ 50 kHz | $V\pi RF_{50\text{ kHz}}$ | - | - | 3 | 3.5 | V |
| Vπ RF @ 1 GHz | $V\pi RF_{1\text{ GHz}}$ | - | - | 3.1 | 3.6 | V |
| Impedance matching | Z_{in-RF} | - | - | 50 | - | Ω |

Optical Characteristics

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|----------------------|-----------|--------------------|------|-------------------------------|------|------|
| Crystal | - | - | | Lithium Niobate Z-Cut, X-Prop | | |
| Waveguide process | - | - | | Ti diffusion | | |
| Operating wavelength | λ | - | 1530 | 1550 | 1570 | nm |
| Insertion loss | IL | Without connectors | - | 2.5 | 3.5 | dB |
| Optical return loss | ORL | - | -40 | -45 | - | dB |

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| Parameter | Symbol | Min | Max | Unit |
|-----------------------|-----------|-----|-----|------|
| RF input power | EP_{in} | - | 33 | dBm |
| Optical input power | OP_{in} | - | 20 | dBm |
| Operating temperature | OT | 0 | +70 | °C |
| Storage temperature | ST | -40 | +85 | °C |

MPZ-LN-10 10 GHz Phase Modulator

Electrical Characteristics

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|-------------------------------------|---------------------------|---------------------------|-----|-----|-----|----------|
| Electro-optic bandwidth | S_{21} | RF electrodes, from 2 GHz | 10 | 12 | - | GHz |
| Ripple S_{21} | ΔS_{21} | - | - | 0.5 | 1 | dB |
| Electrical return loss | S_{11} | - | - | -17 | -14 | dB |
| Electrical return loss - HEP option | S_{11} | - | - | -14 | -10 | dB |
| $V\pi RF @50\text{ kHz}$ | $V\pi RF_{50\text{ kHz}}$ | - | - | 4 | 5 | V |
| $V\pi RF @10\text{ GHz}$ | $V\pi RF_{10\text{ GHz}}$ | - | - | 6 | 7 | V |
| Impedance matching | Z_{in-RF} | - | - | 50 | - | Ω |

Optical Characteristics

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---------------------------|-----------|----------------------------|------|------------------------------|------|------|
| Crystal | - | - | | Lithium Niobate Z-Cut Y-Prop | | |
| Waveguide process | - | - | | Ti diffusion | | |
| Operating wavelength | λ | - | 1530 | 1550 | 1625 | nm |
| Insertion loss | IL | Without optical connectors | - | 2.5 | 3.5 | dB |
| Low insertion loss option | LIL | Without optical connectors | - | 2 | 2.5 | dB |
| Optical return loss | ORL | - | -40 | -45 | - | dB |

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| Parameter | Symbol | Min | Max | Unit |
|------------------------------------|------------|-----|-----|------|
| RF input power | EP_{in} | - | 28 | dBm |
| High electrical input power option | HEP_{in} | - | 33 | dBm |
| Optical input power | OP_{in} | - | 20 | dBm |
| Operating temperature | OT | 0 | +70 | °C |
| Storage temperature | ST | -40 | +85 | °C |

MPZ-LN-20

20 GHz Phase Modulator

Electrical Characteristics

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|-------------------------|---------------------------|---------------------------|-----|-----|-----|------|
| Electro-optic bandwidth | S_{21} | RF electrodes, from 2 GHz | 20 | 25 | - | GHz |
| Ripple S_{21} | ΔS_{21} | - | - | 0.5 | 1 | dB |
| Electrical return loss | S_{11} | - | - | -12 | -10 | dB |
| Vπ RF @ 50 kHz | $V\pi RF_{50\text{ kHz}}$ | - | - | 4.5 | 5.5 | V |
| Vπ RF @ 20 GHz | $V\pi RF_{20\text{ GHz}}$ | - | - | 6.5 | 7.5 | V |
| Impedance matching | Z_{in-RF} | - | - | 50 | - | Ω |

Optical Characteristics

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|----------------------|-----------|--------------------|------|------------------------------|------|------|
| Crystal | - | - | | Lithium Niobate Z-Cut Y-Prop | | |
| Waveguide process | - | - | | Ti diffusion | | |
| Operating wavelength | λ | - | 1530 | 1550 | 1625 | nm |
| Insertion loss | IL | Without connectors | - | 2.5 | 3 | dB |
| Optical return loss | ORL | - | -40 | -45 | - | dB |

All specifications given at 25 °C, 1550 nm, unless differently specified.

Absolute Maximum Ratings

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| Parameter | Symbol | Min | Max | Unit |
|-----------------------|-----------|-----|-----|------|
| RF input power | EP_{in} | - | 28 | dBm |
| Optical input power | OP_{in} | - | 20 | dBm |
| Operating temperature | OT | 0 | +70 | °C |
| Storage temperature | ST | -40 | +85 | °C |

MPZ-LN-40 40 GHz Phase Modulator

Electrical Characteristics

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|----------------------------|----------------------------|---------------------------|-----|-----|-----|----------|
| Electro-optic bandwidth | S_{21} | RF electrodes, from 2 GHz | 30 | 33 | - | GHz |
| Ripple S_{21} | ΔS_{21} | - | - | 0.5 | 1 | dB |
| Electrical return loss | S_{11} | - | - | -12 | -9 | dB |
| $V\pi RF @ 50 \text{ kHz}$ | $V\pi RF_{50 \text{ kHz}}$ | - | - | 6 | 7 | V |
| $V\pi RF @ 30 \text{ GHz}$ | $V\pi RF_{30 \text{ GHz}}$ | - | - | 8.5 | 10 | V |
| Impedance matching | Z_{in-RF} | - | - | 50 | - | Ω |

Optical Characteristics

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|----------------------|-----------|--------------------|------|------------------------------|------|------|
| Crystal | - | - | | Lithium Niobate Z-Cut Y-Prop | | |
| Waveguide process | - | - | | Ti diffusion | | |
| Operating wavelength | λ | - | 1530 | 1550 | 1625 | nm |
| Insertion loss | IL | Without connectors | - | 2.5 | 3 | dB |
| Optical return loss | ORL | - | -40 | -45 | - | dB |

All specifications given at 25 °C, 1550 nm, unless differently specified.

Absolute Maximum Ratings

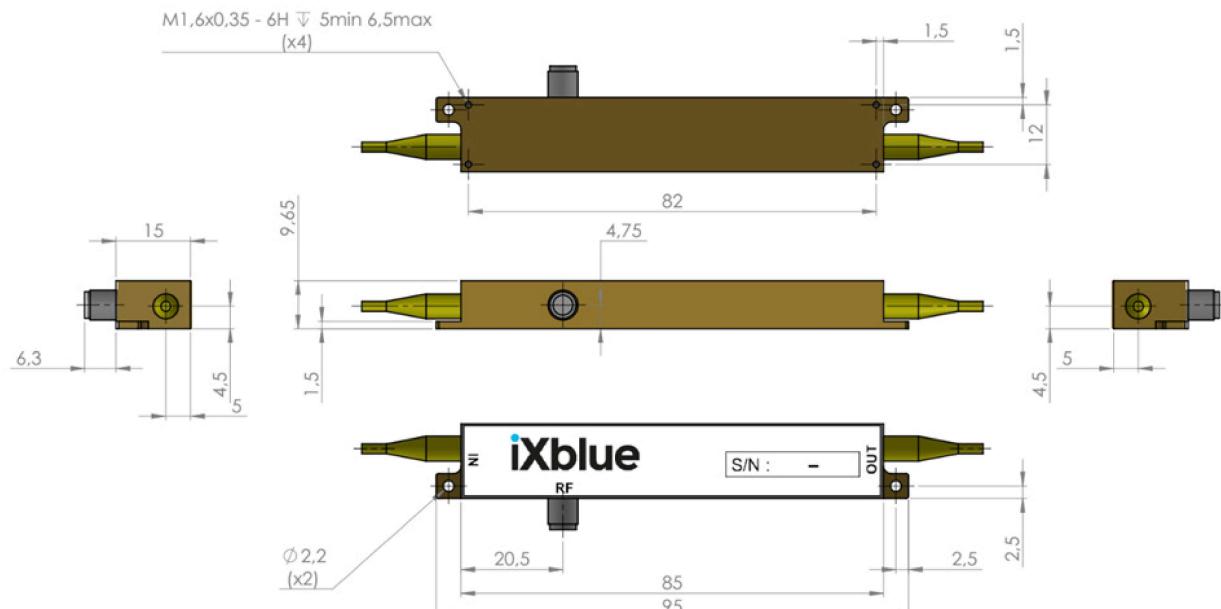
Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. These are absolute stress ratings only. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of the data sheet. Exposure to absolute maximum ratings for extended periods can adversely affect device reliability.

| Parameter | Symbol | Min | Max | Unit |
|-----------------------|-----------|-----|-----|------|
| RF input power | EP_{in} | - | 28 | dBm |
| Optical input power | OP_{in} | - | 20 | dBm |
| Operating temperature | OT | 0 | +70 | °C |
| Storage temperature | ST | -40 | +85 | °C |

MODULATOR

Mechanical Diagram and Pinout

All measurements in mm



| Port | Function | Note |
|------|---------------------|---|
| IN | Optical input port | Polarization maintaining 1550 nm Corning PM 15-U25D length : 1.5 meter, buffer diameter : 900 um |
| OUT | Optical output port | Polarization maintaining 1550 nm Corning PM 15-U25D length : 1.5 meter, buffer diameter : 900 um |
| RF | RF input port | Female K MPZ-LN-40: 2.4 mm, female, compatible to mate with V / 1.85 mm connectors (K Option) |

Ordering information

MPX-LN-XX-00-P-P-AB-CD / MPZ-LN-WW-00-P-P-AB-CD

-POL

-HEP

-LIL

XX = X-cut Bandwidth: 0.1 150 MHz

WW = Z-cut Bandwidth : 01 01 GHz 10 10 GHz 20 20 GHz 40 40 GHz

P = Single Mode and Polarization Maintaining fiber

AB = Input connector : 00 bare fiber FA FC/APC FC FC/SPC

CD = Output connector : 00 bare fiber FA FC/APC FC FC/SPC

POL = Embedded in-line POLarizer

HEP = High Electrical Power option for the MPZ-LN-10 only

LIL = Low Insertion Loss option for the MPZ-LN-10 only

Note : optical connectors are Senko with narrow key or equivalent

About us

iXblue Photonics produces specialty optical fibers and Bragg gratings based fiber optics components and provides optical modulation solutions based on the company lithium niobate (LiNbO_3) modulators and RF electronic modules.

iXblue Photonics serves a wide range of industries: sensing and instruments, defense, telecommunications, space and fiber lasers as well as research laboratories all over the world.

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